

## TS3USB221 High-Speed USB 2.0 (480-Mbps) 1:2 Multiplexer – Demultiplexer Switch With Single Enable

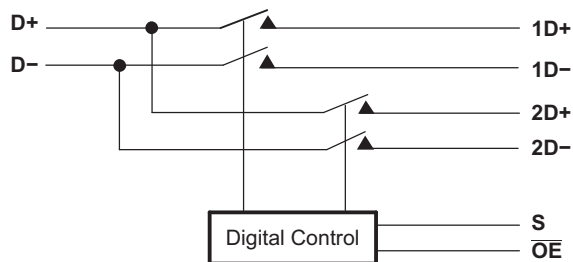
### 1 Features

- $V_{CC}$  Operation from 2.3 V and 3.6 V
- $V_{I/O}$  Accepts Signals up to 5.5 V
- 1.8-V Compatible Control-Pin Inputs
- Low-Power Mode When  $\overline{OE}$  Is Disabled (1  $\mu$ A)
- $r_{ON} = 6 \Omega$  Maximum
- $\Delta r_{ON} = 0.2 \Omega$  Typical
- $C_{io(on)} = 6$  pF Maximum
- Low Power Consumption (30  $\mu$ A Maximum)
- ESD > 2000-V Human-Body Model (HBM)
- High Bandwidth (1.1 GHz Typical)

### 2 Applications

- Routes Signals for USB 1.0, 1.1, and 2.0
- Mobile Industry Processor Interface (MIPI™) Signal Routing
- MHL 1.0

Block Diagram



### 3 Description

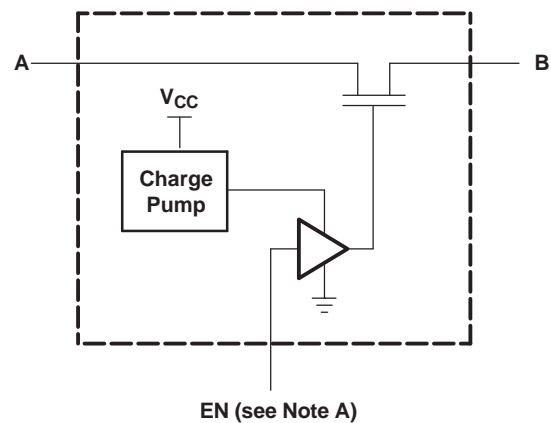
The TS3USB221 is a high-bandwidth switch specially designed for the switching of high-speed USB 2.0 signals in handset and consumer applications, such as cell phones, digital cameras, and notebooks with hubs or controllers with limited USB I/Os. The wide bandwidth (1.1 GHz) of this switch allows signals to pass with minimum edge and phase distortion. The device multiplexes differential outputs from a USB host device to one of two corresponding outputs. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. The TS3USB221 is designed for low bit-to-bit skew and high channel to channel noise isolation. The TS3USB221 is also compatible with various standards, such as high-speed USB 2.0 (480 Mbps).

Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TS3USB221	VSON (10)	3.00 mm x 3.00 mm
	UQFN (10)	1.50 mm x 2.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic, Each FET Switch (SW)



- A. EN is the internal enable signal applied to the switch.



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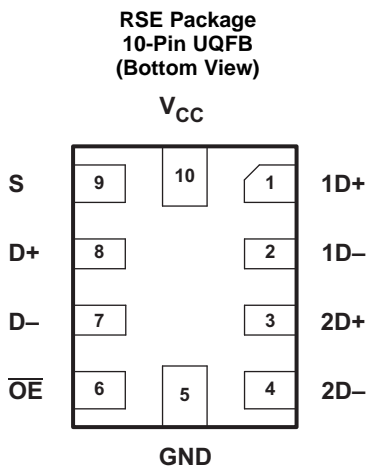
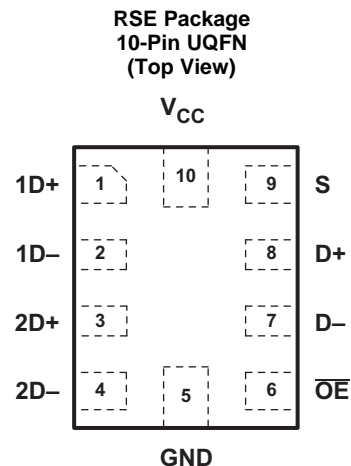
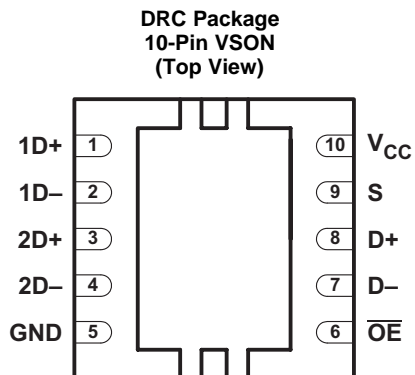
## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision H (February 2015) to Revision I	Page
• Changed $V_{IH}$ Max from 5.5 to $V_{CC}$ in <i>Recommended Operating Conditions</i> table .....	4

Changes from Revision G (September 2010) to Revision H	Page
• Changed first bullet of the Features FROM: $V_{CC}$ Operation at 2.5 V and 3.3 V TO: $V_{CC}$ Operation at 2.3 V and 3.6 V .....	1
• Added <i>Pin Configuration and Functions</i> section, <i>ESD Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i> , <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section .....	1
• Removed the <i>Ordering Information</i> table .....	1

## 5 Pin Configuration and Functions



### Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1D+	1	I/O	USB port 1
1D-	2	I/O	
2D+	3	I/O	USB port 2
2D-	4	I/O	
GND	5	—	Ground
$\overline{\text{OE}}$	6	I	Bus-switch enable
D-	7	I/O	Common USB port
D+	8	I/O	
S	9	I	Select input
V <sub>CC</sub>	10	—	Supply voltage

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	-0.5	4.6	V
V <sub>IN</sub>	Control input voltage <sup>(2) (3)</sup>	-0.5	7	V
V <sub>I/O</sub>	Switch I/O voltage <sup>(2) (3) (4)</sup>	-0.5	7	V
I <sub>IK</sub>	Control input clamp current	V <sub>IN</sub> < 0	-50	mA
I <sub>I/O</sub>	I/O port clamp current	V <sub>I/O</sub> < 0	-50	mA
I <sub>I/O</sub>	ON-state switch current <sup>(5)</sup>		±120	mA
	Continuous current through V <sub>CC</sub> or GND		±100	mA
T <sub>stg</sub>	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground, unless otherwise specified.
- (3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (4) V<sub>I</sub> and V<sub>O</sub> are used to denote specific conditions for V<sub>I/O</sub>.
- (5) I<sub>I</sub> and I<sub>O</sub> are used to denote specific conditions for I<sub>I/O</sub>.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001	2000 V

### 6.3 Recommended Operating Conditions

See <sup>(1)</sup>.

		MIN	MAX	UNIT	
V <sub>CC</sub>	Supply voltage	2.3	3.6	V	
V <sub>IH</sub>	High-level control input voltage	0.46 × V <sub>CC</sub>	V <sub>CC</sub>	V	
V <sub>IL</sub>	Low-level control input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	0	0.25 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.7 V to 3.6 V			
V <sub>I/O</sub>	Data input/output voltage	0	5.5	V	
T <sub>A</sub>	Operating free-air temperature	-40	85	°C	

- (1) All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TS3USB221		UNIT
		DRC (VSON)	RSE (UQFN)	
		10 PINS	10 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	57.7	169.8	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	87.7	84.7	
R <sub>θJB</sub>	Junction-to-board thermal resistance	32.6	94.9	
ψ <sub>JT</sub>	Junction-to-top characterization parameter	8.2	5.7	
ψ <sub>JB</sub>	Junction-to-board characterization parameter	32.8	94.9	
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	18.5	N/A	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

PARAMETER	TEST CONDITIONS		MIN	TYP <sup>(2)</sup>	MAX	UNIT
$V_{IK}$	$V_{CC} = 3.6\text{ V}, 2.7\text{ V}, I_I = -18\text{ mA}$				-1.8	V
$I_{IN}$	Control inputs	$V_{CC} = 3.6\text{ V}, 2.7\text{ V}, 0\text{ V}, V_{IN} = 0\text{ V to } 3.6\text{ V}$			±1	µA
$I_{OZ}$ <sup>(3)</sup>		$V_{CC} = 3.6\text{ V}, 2.7\text{ V}, V_O = 0\text{ V to } 3.6\text{ V}, V_I = 0\text{ V}, V_{IN} = V_{CC}\text{ or GND}, \text{Switch OFF}$			±1	µA
$I_{OFF}$		$V_{CC} = 0\text{ V}$	$V_{I/O} = 0\text{ V to } 3.6\text{ V}$		±2	µA
			$V_{I/O} = 0\text{ V to } 2.7\text{ V}$		±1	
$I_{CC}$		$V_{CC} = 3.6\text{ V}, 2.7\text{ V}, V_{IN} = V_{CC}\text{ or GND}, I_{I/O} = 0\text{ V}, \text{Switch ON or OFF}$			30	µA
$I_{CC}$ (low power mode)		$V_{CC} = 3.6\text{ V}, 2.7\text{ V}, V_{IN} = V_{CC}\text{ or GND}, \text{Switch disabled (OE in high state)}$			1	µA
$\Delta I_{CC}$ <sup>(4)</sup>	Control inputs	One input at 1.8 V, Other inputs at $V_{CC}$ or GND	$V_{CC} = 3.6\text{ V}$		20	µA
			$V_{CC} = 2.7\text{ V}$		0.5	
$C_{in}$	Control inputs	$V_{CC} = 3.3\text{ V}, 2.5\text{ V}, V_{IN} = 3.3\text{ V or } 0\text{ V}$		1	2	pF
$C_{io(OFF)}$		$V_{CC} = 3.3\text{ V}, 2.5\text{ V}, V_{I/O} = 3.3\text{ V or } 0\text{ V}, \text{Switch OFF}$		3	4	pF
$C_{io(ON)}$		$V_{CC} = 3.3\text{ V}, 2.5\text{ V}, V_{I/O} = 3.3\text{ V or } 0\text{ V}, \text{Switch ON}$		5	6	pF
$r_{on}$ <sup>(5)</sup>		$V_{CC} = 3\text{ V}, 2.3\text{ V}$	$V_I = 0\text{ V}, I_O = 30\text{ mA}$		6	Ω
			$V_I = 2.4\text{ V}, I_O = -15\text{ mA}$		6	
$\Delta r_{on}$		$V_{CC} = 3\text{ V}, 2.3\text{ V}$	$V_I = 0\text{ V}, I_O = 30\text{ mA}$	0.2		Ω
			$V_I = 1.7, I_O = -15\text{ mA}$	0.2		
$r_{on(Flat)}$		$V_{CC} = 3\text{ V}, 2.3\text{ V}$	$V_I = 0\text{ V}, I_O = 30\text{ mA}$	1		Ω
			$V_I = 1.7, I_O = -15\text{ mA}$	1		

(1)  $V_{IN}$  and  $I_{IN}$  refer to control inputs.  $V_I$ ,  $V_O$ ,  $I_I$ , and  $I_O$  refer to data pins.

(2) All typical values are at  $V_{CC} = 3.3\text{ V}$  (unless otherwise noted),  $T_A = 25^\circ\text{C}$ .

(3) For I/O ports, the parameter  $I_{OZ}$  includes the input leakage current.

(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than  $V_{CC}$  or GND.

(5) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

## 6.6 Dynamic Electrical Characteristics, $V_{CC} = 3.3 V \pm 10\%$

 over operating range,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$ ,  $V_{CC} = 3.3 V \pm 10\%$ ,  $GND = 0 V$ 

PARAMETER		TEST CONDITIONS	TYP <sup>(1)</sup>	UNIT
$X_{TALK}$	Crosstalk	$R_L = 50 \Omega$ , $f = 250 \text{ MHz}$	-40	dB
$O_{IRR}$	OFF isolation	$R_L = 50 \Omega$ , $f = 250 \text{ MHz}$	-41	dB
BW	Bandwidth (-3 dB)	$R_L = 50 \Omega$	1.1	GHz

 (1) For Maximum or Minimum conditions, use the appropriate value specified under [Electrical Characteristics](#) for the applicable device type.

## 6.7 Dynamic Electrical Characteristics, $V_{CC} = 2.5 V \pm 10\%$

 over operating range,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$ ,  $V_{CC} = 2.5 V \pm 10\%$ ,  $GND = 0 V$ 

PARAMETER		TEST CONDITIONS	TYP <sup>(1)</sup>	UNIT
$X_{TALK}$	Crosstalk	$R_L = 50 \Omega$ , $f = 250 \text{ MHz}$	-39	dB
$O_{IRR}$	OFF isolation	$R_L = 50 \Omega$ , $f = 250 \text{ MHz}$	-40	dB
BW	Bandwidth (-3 dB)	$R_L = 50 \Omega$	1.1	GHz

 (1) For Maximum or Minimum conditions, use the appropriate value specified under [Electrical Characteristics](#) for the applicable device type.

## 6.8 Switching Characteristics, $V_{CC} = 3.3 V \pm 10\%$

 over operating range,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$ ,  $V_{CC} = 3.3 V \pm 10\%$ ,  $GND = 0 V$ 

PARAMETER		MIN	TYP <sup>(1)</sup>	MAX	UNIT
$t_{pd}$	Propagation delay <sup>(2) (3)</sup>		0.25		ns
$t_{ON}$	Line enable time	S to D, nD		30	ns
		$\overline{OE}$ to D, nD		17	
$t_{OFF}$	Line disable time	S to D, nD		12	ns
		$\overline{OE}$ to D, nD		10	
$t_{SK(O)}$	Output skew between center port to any other port <sup>(2)</sup>		0.1	0.2	ns
$t_{SK(P)}$	Skew between opposite transitions of the same output ( $t_{PHL} - t_{PLH}$ ) <sup>(2)</sup>		0.1	0.2	ns

 (1) For Maximum or Minimum conditions, use the appropriate value specified under [Electrical Characteristics](#) for the applicable device type.

(2) Specified by design

(3) The bus switch contributes no propagational delay other than the RC delay of the on resistance of the switch and the load capacitance. The time constant for the switch alone is of the order of 0.25 ns for 10-pF load. This time constant adds very little propagational delay to the system because it is much smaller than the rise/fall times of typical driving signals. Propagational delay of the bus switch, when used in a system, is determined by the driving circuit on the driving side of the switch and its interactions with the load on the driven side.

## 6.9 Switching Characteristics, $V_{CC} = 2.5 V \pm 10\%$

 over operating range,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$ ,  $V_{CC} = 2.5 V \pm 10\%$ ,  $GND = 0 V$ 

PARAMETER		MIN	TYP <sup>(1)</sup>	MAX	UNIT
$t_{pd}$	Propagation delay <sup>(2) (3)</sup>		0.25		ns
$t_{ON}$	Line enable time	S to D, nD		50	ns
		$\overline{OE}$ to D, nD		32	
$t_{OFF}$	Line disable time	S to D, nD		23	ns
		$\overline{OE}$ to D, nD		12	
$t_{SK(O)}$	Output skew between center port to any other port <sup>(2)</sup>		0.1	0.2	ns
$t_{SK(P)}$	Skew between opposite transitions of the same output ( $t_{PHL} - t_{PLH}$ ) <sup>(2)</sup>		0.1	0.2	ns

 (1) For Maximum or Minimum conditions, use the appropriate value specified under [Electrical Characteristics](#) for the applicable device type.

(2) Specified by design

(3) The bus switch contributes no propagational delay other than the RC delay of the on resistance of the switch and the load capacitance. The time constant for the switch alone is of the order of 0.25 ns for 10-pF load. The time constraint adds very little propagational delay to the system because it is much smaller than the rise and fall times of typical driving signals. Propagational delay of the bus switch, when used in a system, is determined by the driving circuit on the driving side of the switch and its interactions with the load on the driven side.

## 6.10 Typical Characteristics

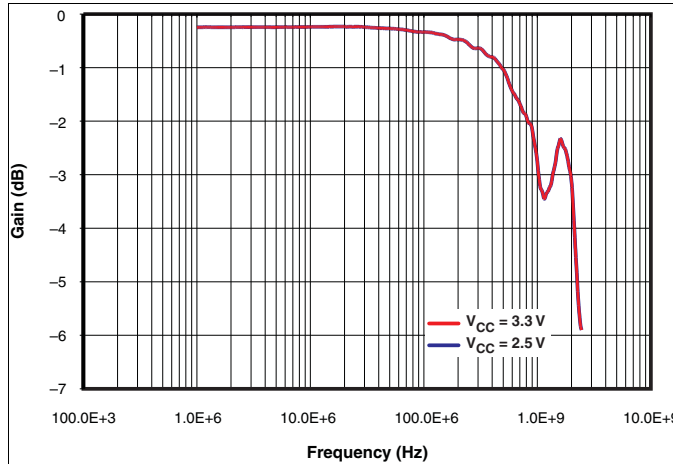


Figure 1. Gain vs Frequency

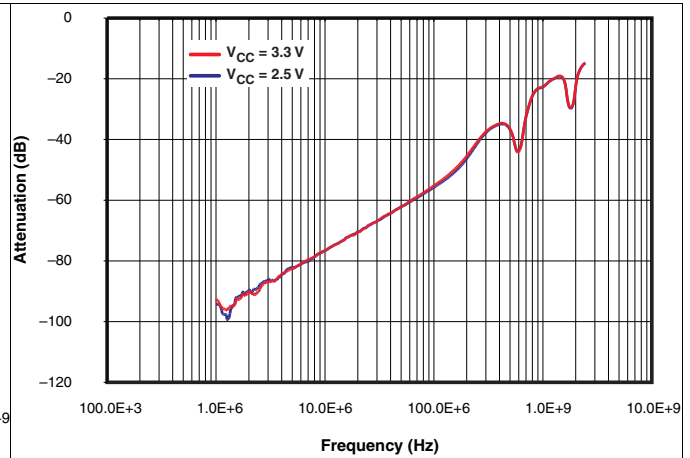


Figure 2. OFF Isolation vs Frequency

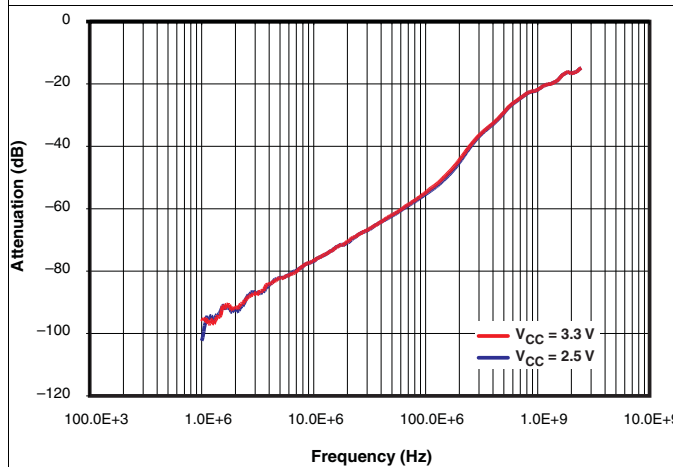


Figure 3. Crosstalk vs Frequency

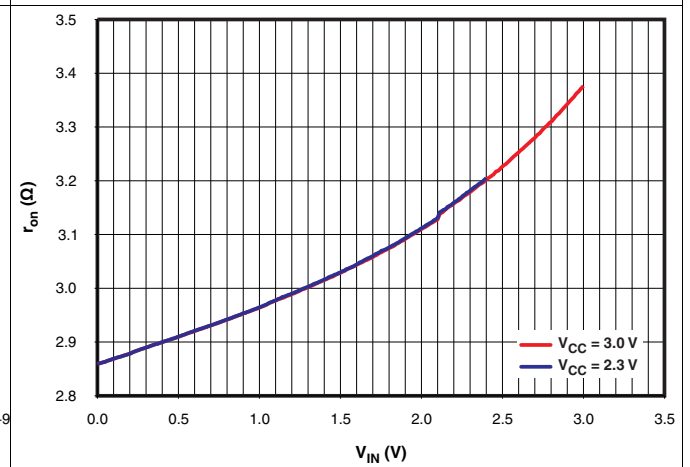


Figure 4.  $r_{on}$  vs  $V_{IN}$  ( $I_{OUT} = -15$  mA)

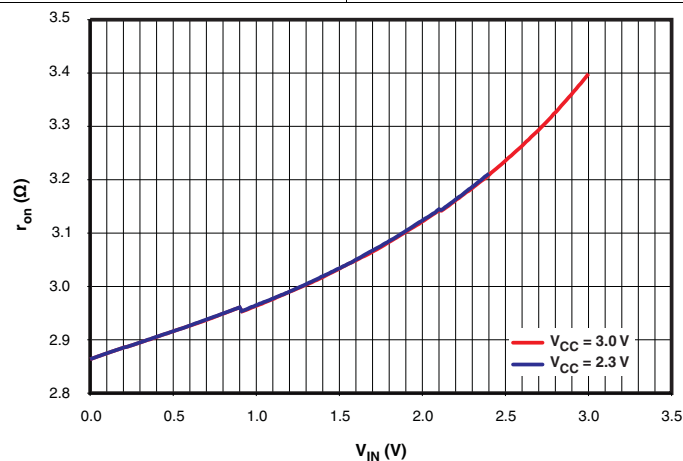
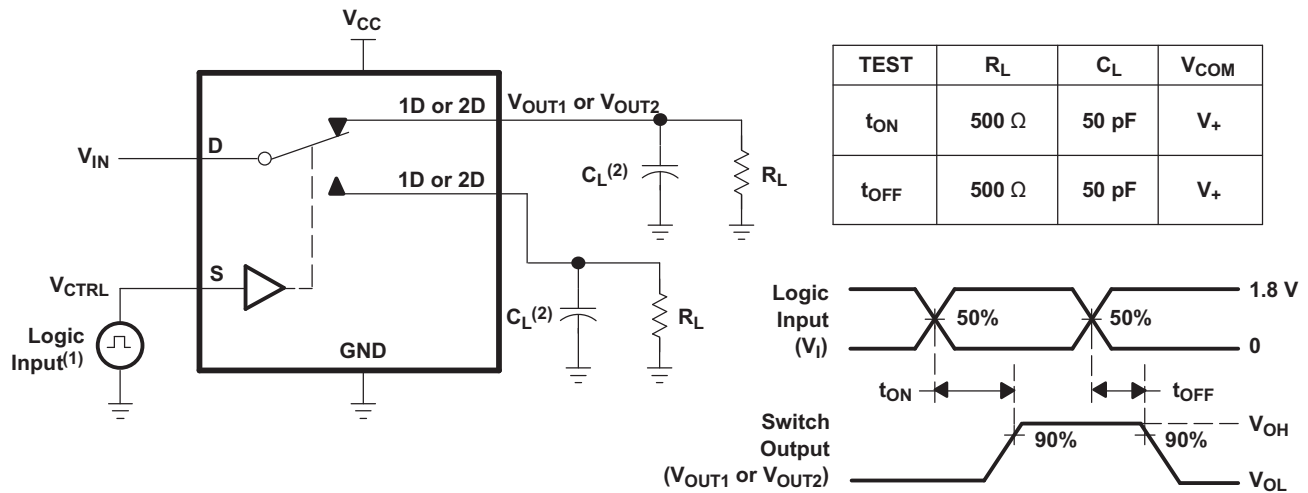


Figure 5.  $r_{on}$  vs  $V_{IN}$  ( $I_{OUT} = -30$  mA)

## 7 Parameter Measurement Information



- (1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z<sub>O</sub> = 50 Ω, t<sub>r</sub> < 5 ns, t<sub>f</sub> < 5 ns.
- (2) C<sub>L</sub> includes probe and jig capacitance.

Figure 6. Turnon (t<sub>ON</sub>) and Turnoff Time (t<sub>OFF</sub>)

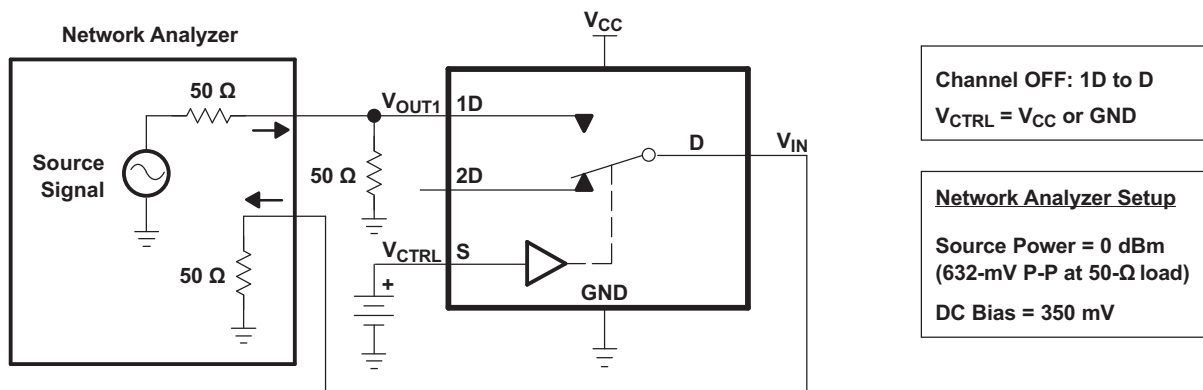


Figure 7. OFF Isolation (O<sub>ISO</sub>)

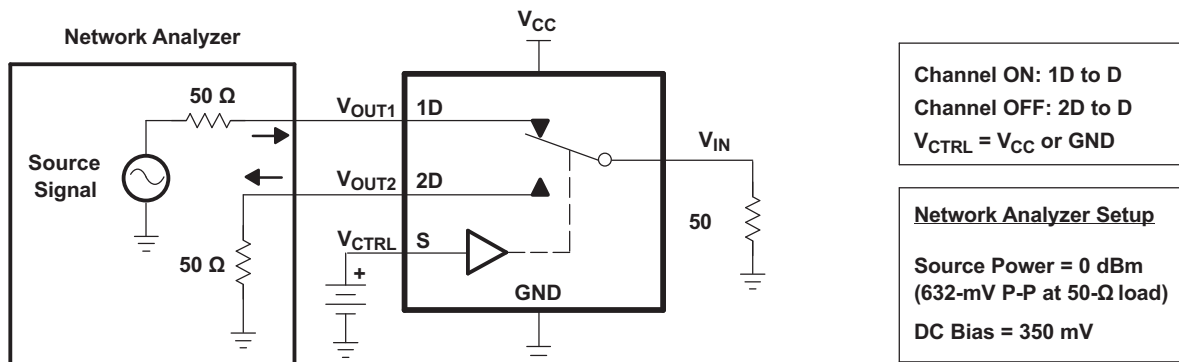


Figure 8. Crosstalk (X<sub>TALK</sub>)



Parameter Measurement Information (continued)

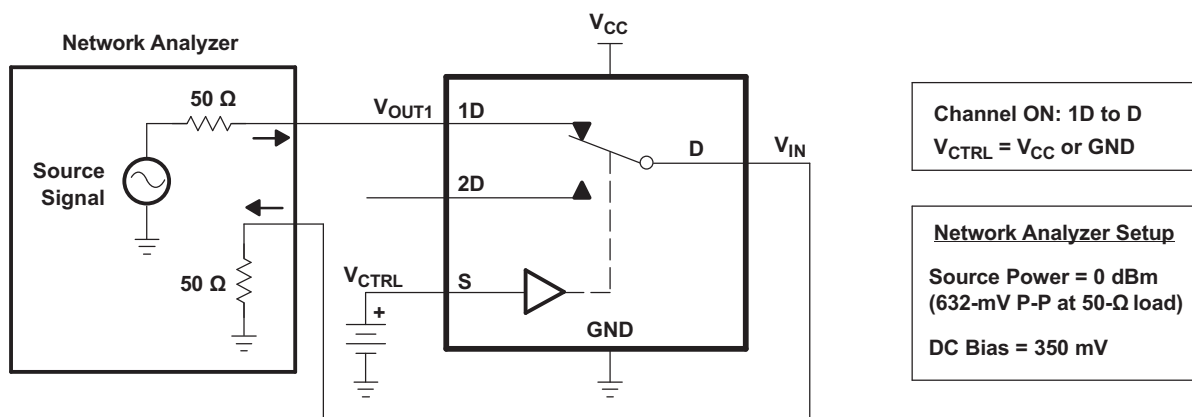


Figure 9. Bandwidth (BW)

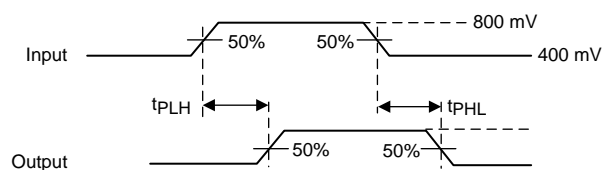


Figure 10. Propagation Delay

Parameter Measurement Information (continued)

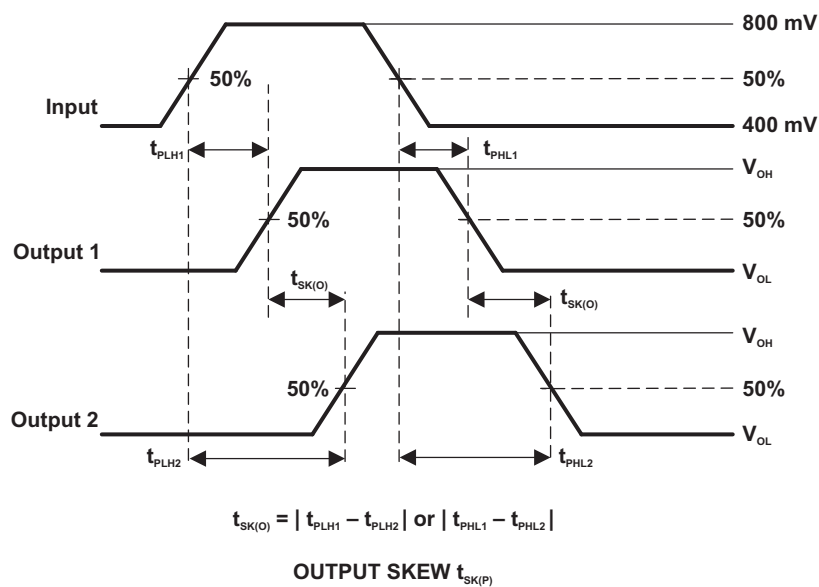
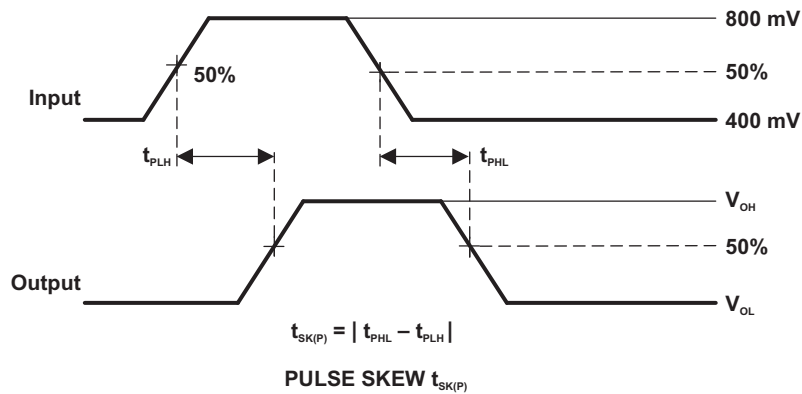


Figure 11. Skew Test

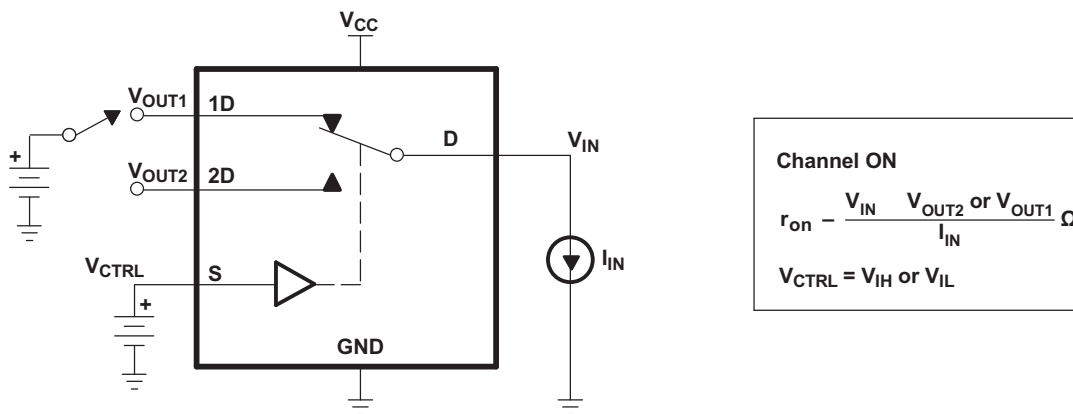


Figure 12. ON-State Resistance ( $r_{on}$ )

Parameter Measurement Information (continued)

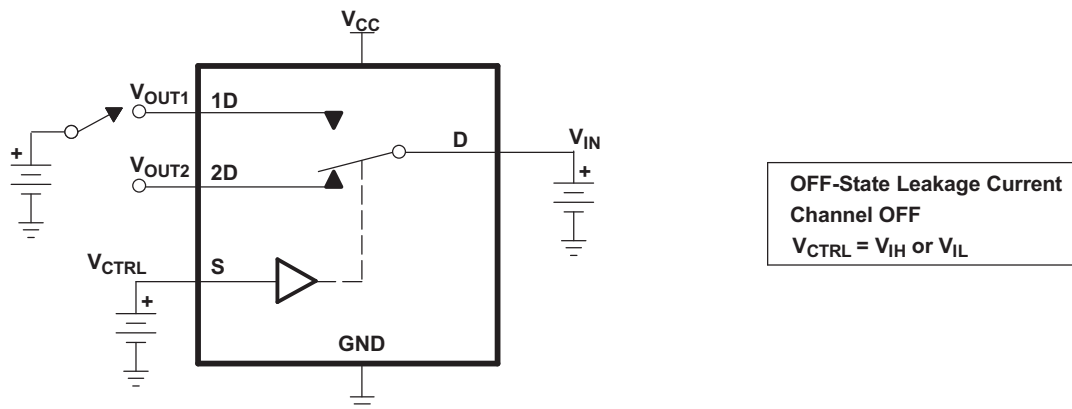


Figure 13. OFF-State Leakage Current

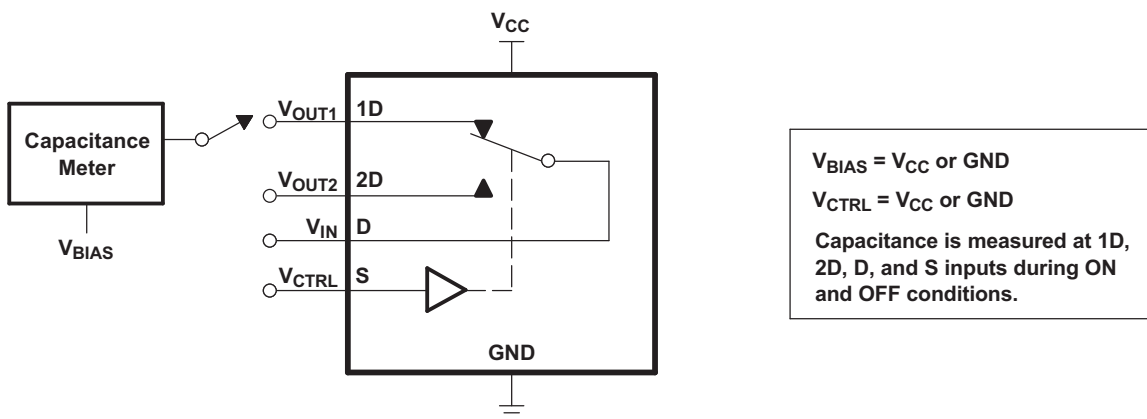


Figure 14. Capacitance

## 8 Detailed Description

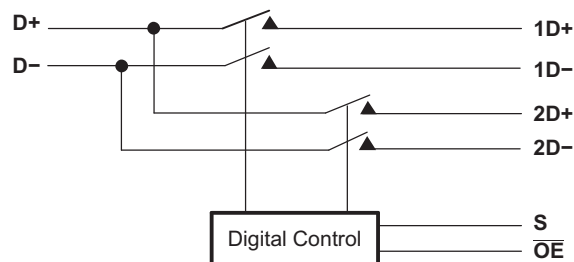
### 8.1 Overview

The TS3USB221 device is a 2-channel SPDT switch specially designed for the switching of high-speed USB 2.0 signals in handset and consumer applications, such as cell phones, digital cameras, and notebooks with hubs or controllers with limited USB I/Os. The wide bandwidth (1.1 GHz) of this switch allows signals to pass with minimum edge and phase distortion. The device multiplexes differential outputs from a USB host device to one of two corresponding outputs. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. The device also has a low power mode that reduces the power consumption to 1  $\mu$ A for portable applications with a battery or limited power budget.

The device is designed for low bit-to-bit skew and high channel-to-channel noise isolation, and is compatible with various standards, such as high-speed USB 2.0 (480 Mbps).

The TS3USB221 device integrates ESD protection cells on all pins, is available in a tiny  $\mu$ QFN package (2 mm  $\times$  1.5 mm) and is characterized over the free-air temperature range from  $-40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$ .

### 8.2 Functional Block Diagram



### 8.3 Feature Description

#### 8.3.1 Low Power Mode

The TS3USB221 has a low power mode that reduces the power consumption to 1  $\mu$ A when the device is not in use. The bus-switch enable pin  $\overline{\text{OE}}$  must be supplied with a logic high signal to put the device in low power mode and disable the switch.

### 8.4 Device Functional Modes

**Table 1. Truth Table**

S	$\overline{\text{OE}}$	FUNCTION
X	H	Disconnect
L	L	D = 1D
H	L	D = 2D

## 9 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

There are many USB applications in which the USB hubs or controllers have a limited number of USB I/Os. The TS3USB221 solution can effectively expand the limited USB I/Os by switching between multiple USB buses in order to interface them to a single USB hub or controller. TS3USB221 can also be used to connect a single controller to two USB connectors.

### 9.2 Typical Application

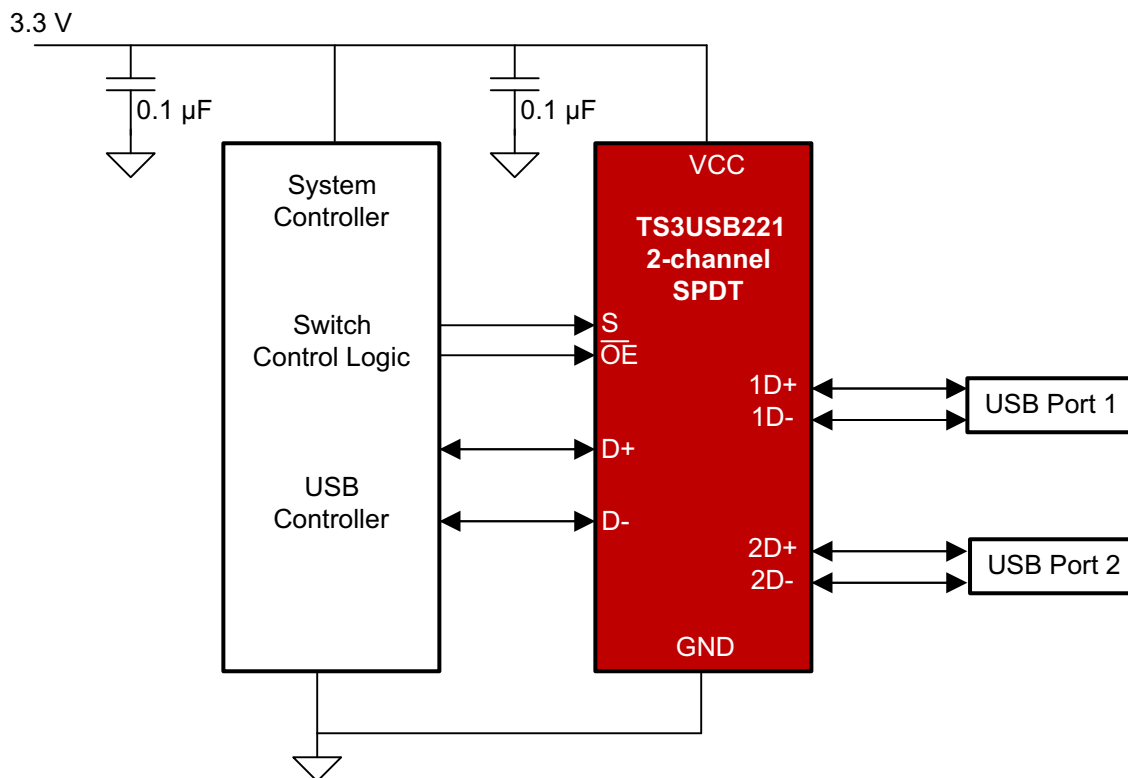


Figure 15. Simplified Schematic

#### 9.2.1 Design Requirements

Design requirements of the USB 1.0, 1.1, and 2.0 standards should be followed.

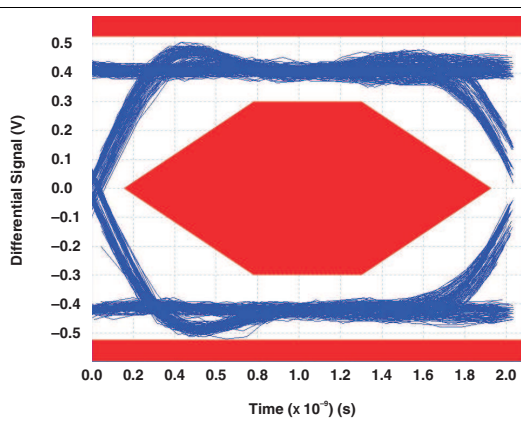
TI recommends that the digital control pins S and  $\overline{OE}$  be pulled up to  $V_{CC}$  or down to GND to avoid undesired switch positions that could result from the floating pin.

#### 9.2.2 Detailed Design Procedure

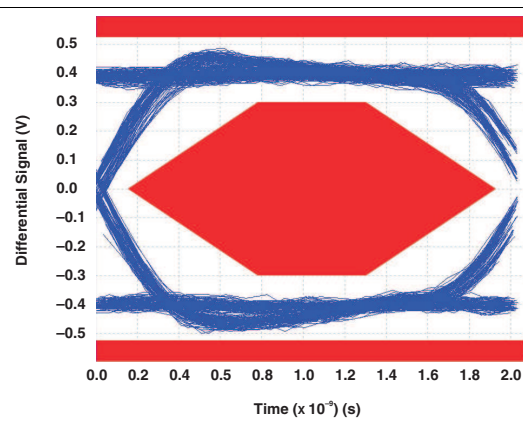
The TS3USB221 may be properly operated without any external components. However, it is recommended that unused pins be connected to ground through a 50-Ω resistor to prevent signal reflections back into the device.

**Typical Application (continued)**

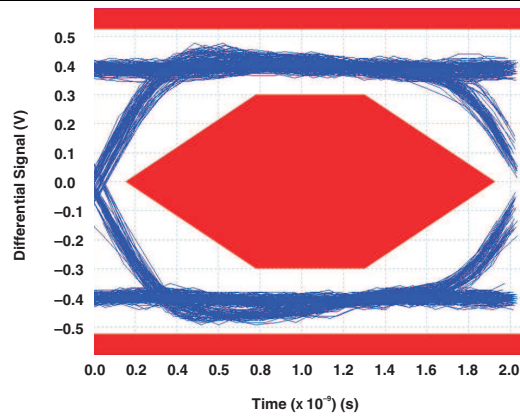
**9.2.3 Application Curves**



**Figure 16. Eye Pattern: 480-Mbps USB Signal With No Switch (Through Path)**



**Figure 17. Eye Pattern: 480-Mbps USB Signal With Switch NC Path**



**Figure 18. Eye Pattern: 480-Mbps USB Signal With Switch NO Path**

## 10 Power Supply Recommendations

Power to the device is supplied through the  $V_{CC}$  pin and should follow the USB 1.0, 1.1, and 2.0 standards. TI recommends placing a bypass capacitor as close as possible to the supply pin  $V_{CC}$  to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

## 11 Layout

### 11.1 Layout Guidelines

Place supply bypass capacitors as close to  $V_{CC}$  pin as possible. Avoid placing the bypass caps near the D+/D– traces.

The high-speed D+/D– traces should always be matched lengths and must be no more than 4 inches, otherwise the eye diagram performance may be degraded. A high-speed USB connection is made through a shielded, twisted pair cable with a differential characteristic impedance. In the layout, the impedance of D+ and D– traces should match the cable characteristic differential impedance for optimal performance.

Route the high-speed USB signals using a minimum of vias and corners which will reduce signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points on twisted pair lines; through-hole pins are not recommended.

When it becomes necessary to turn 90°, use two 45° turns or an arc instead of making a single 90° turn. This reduces reflections on the signal traces by minimizing impedance discontinuities.

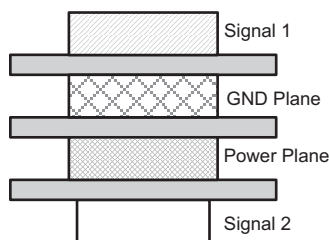
Do not route USB traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices or IC's that use or duplicate clock signals.

Avoid stubs on the high-speed USB signals because they cause signal reflections. If a stub is unavoidable, then the stub should be less than 200 mm.

Route all high-speed USB signal traces over continuous planes ( $V_{CC}$  or GND), with no interruptions.

Avoid crossing over anti-etch, commonly found with plane splits.

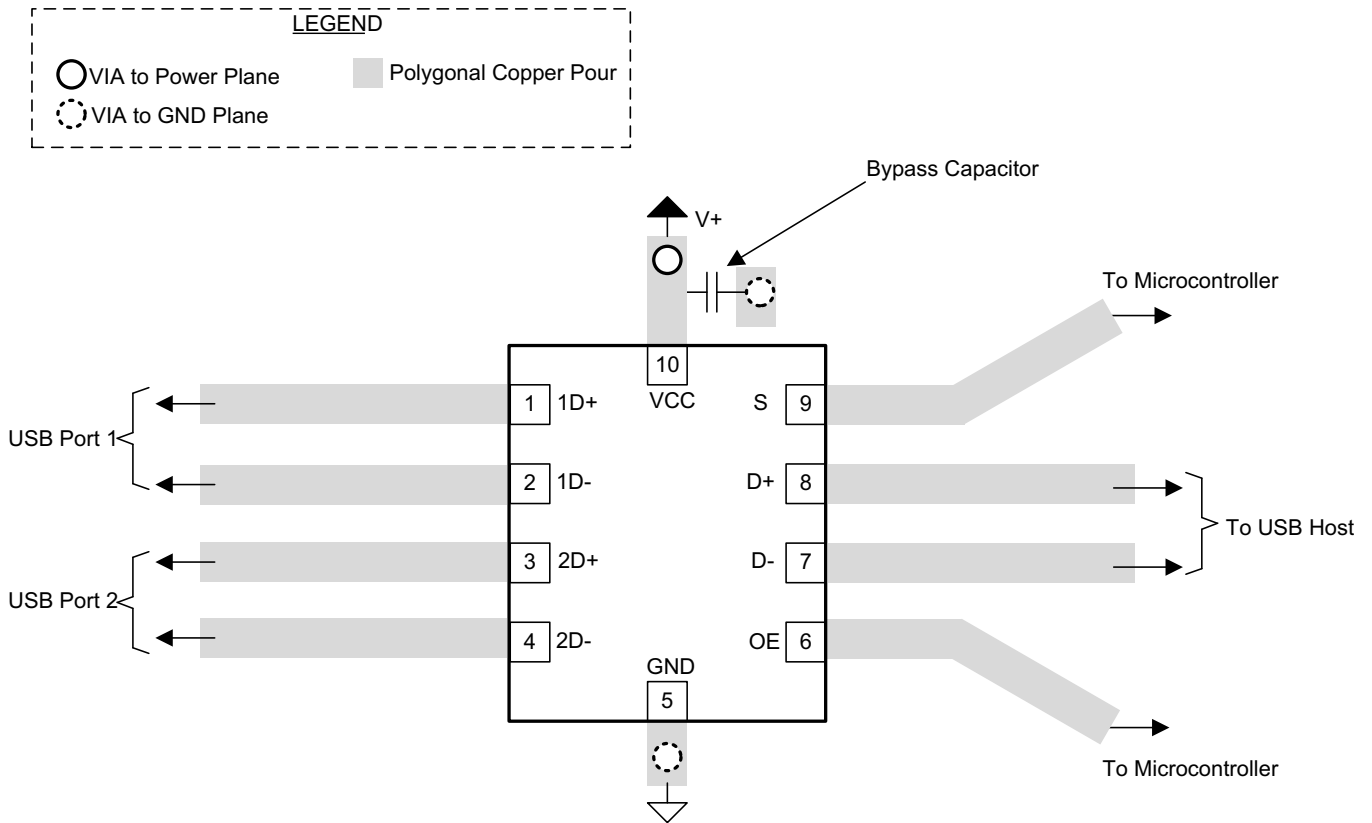
A printed circuit board with at least four layers is recommended because of high frequencies associated with the USB; two signal layers separated by a ground and power layer as shown in [Figure 19](#).



**Figure 19. Four-Layer Board Stack-Up**

The majority of signal traces should run on a single layer, preferably Signal 1. Immediately next to this layer should be the GND plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies. For more information on layout guidelines, see *High Speed Layout Guidelines (SCAA082)* and *USB 2.0 Board Design and Layout Guidelines (SPRAAR7)*.

## 11.2 Layout Example



**Figure 20. Package Layout Diagram**



## 12 Device and Documentation Support

### 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation, see the following:

- *High Speed Layout Guidelines*, [SCAA082](#)
- *USB 2.0 Board Design and Layout Guidelines*, [SPRAAR7](#)

### 12.2 Trademarks

MIPI is a trademark of Mobile Industry Processor Interface Alliance. All other trademarks are the property of their respective owners.

### 12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 12.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN080104RSER	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(L57 ~ L5O ~ L5R ~ L5V)	<a href="#">Samples</a>
TS3USB221DRCR	ACTIVE	VSON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU   CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 85	ZWG	<a href="#">Samples</a>
TS3USB221DRCRG4	ACTIVE	VSON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZWG	<a href="#">Samples</a>
TS3USB221RSER	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU   CU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(L57 ~ L5O ~ L5R ~ L5V)	<a href="#">Samples</a>
TS3USB221RSERG4	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(L57 ~ L5O ~ L5R ~ L5V)	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3USB221DRCR	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
TS3USB221RSER	UQFN	RSE	10	3000	180.0	9.5	1.7	2.2	0.75	4.0	8.0	Q1
TS3USB221RSER	UQFN	RSE	10	3000	180.0	9.5	1.7	2.3	0.75	4.0	8.0	Q1
TS3USB221RSER	UQFN	RSE	10	3000	180.0	8.4	1.68	2.13	0.76	4.0	8.0	Q1

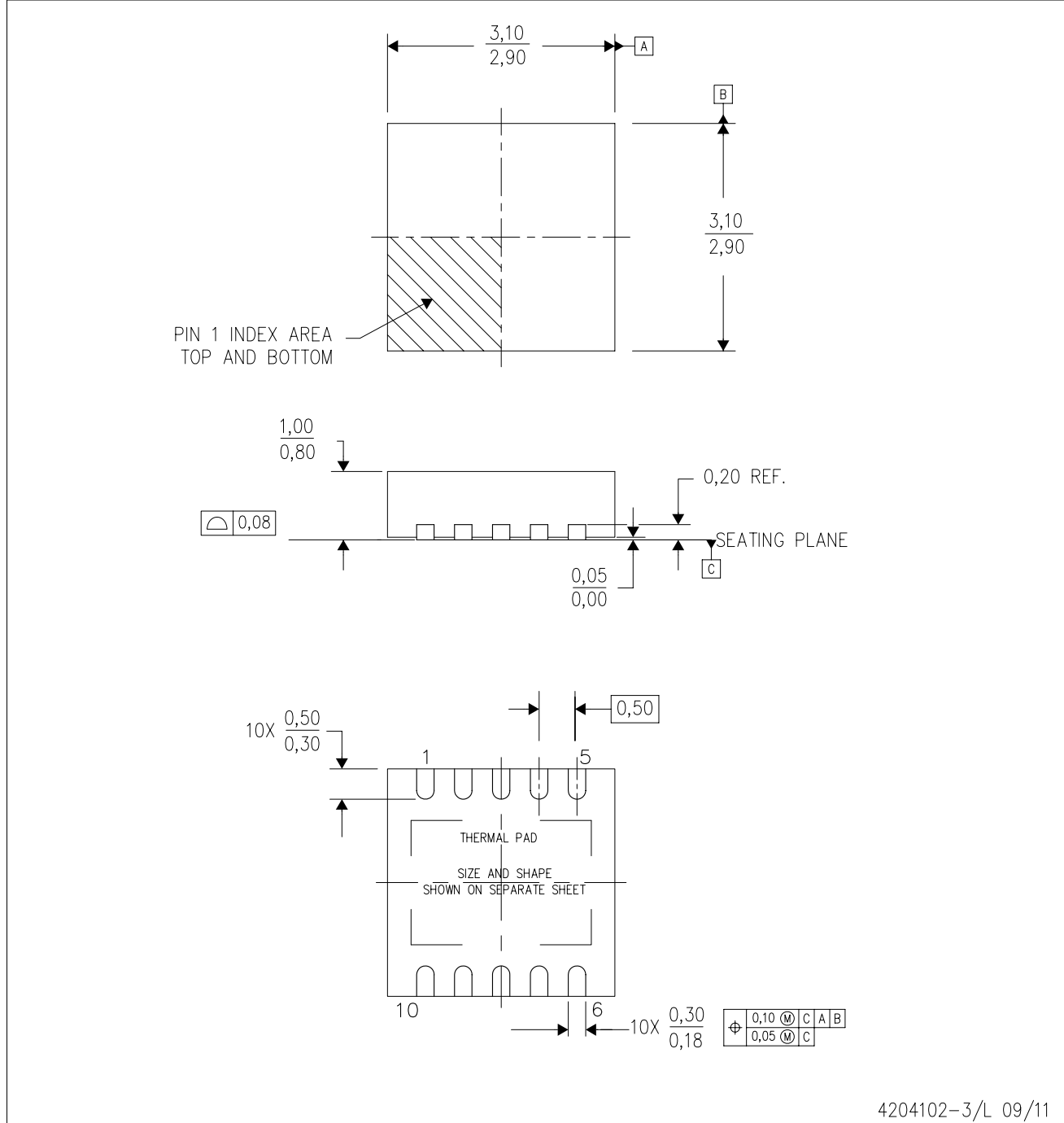
**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3USB221DRCR	VSON	DRC	10	3000	370.0	355.0	55.0
TS3USB221RSER	UQFN	RSE	10	3000	189.0	185.0	36.0
TS3USB221RSER	UQFN	RSE	10	3000	184.0	184.0	19.0
TS3USB221RSER	UQFN	RSE	10	3000	202.0	201.0	28.0

DRC (S-PVSON-N10)

PLASTIC SMALL OUTLINE NO-LEAD



4204102-3/L 09/11

- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - This drawing is subject to change without notice.
  - Small Outline No-Lead (SON) package configuration.
  - The package thermal pad must be soldered to the board for thermal and mechanical performance, if present.
  - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions, if present

# THERMAL PAD MECHANICAL DATA

DRC (S-PVSON-N10)

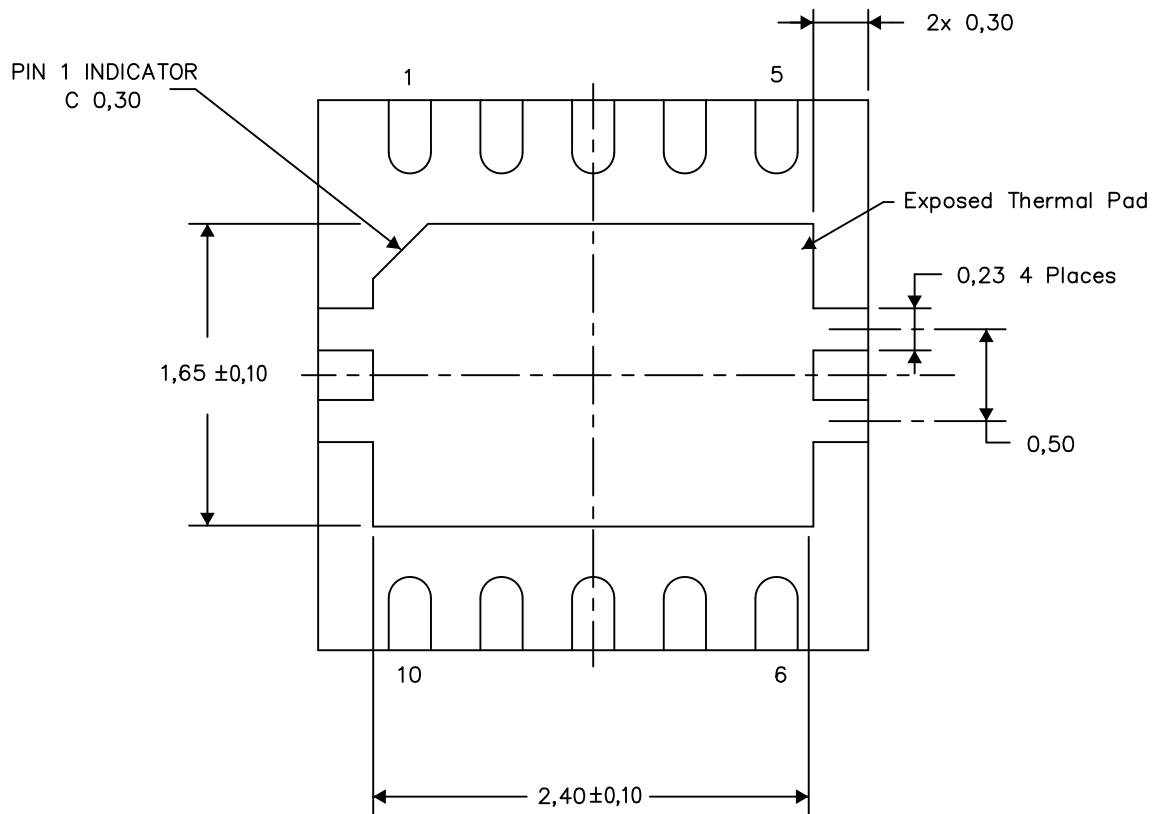
PLASTIC SMALL OUTLINE NO-LEAD

## THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at [www.ti.com](http://www.ti.com).

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

4206565-3/Y 08/15

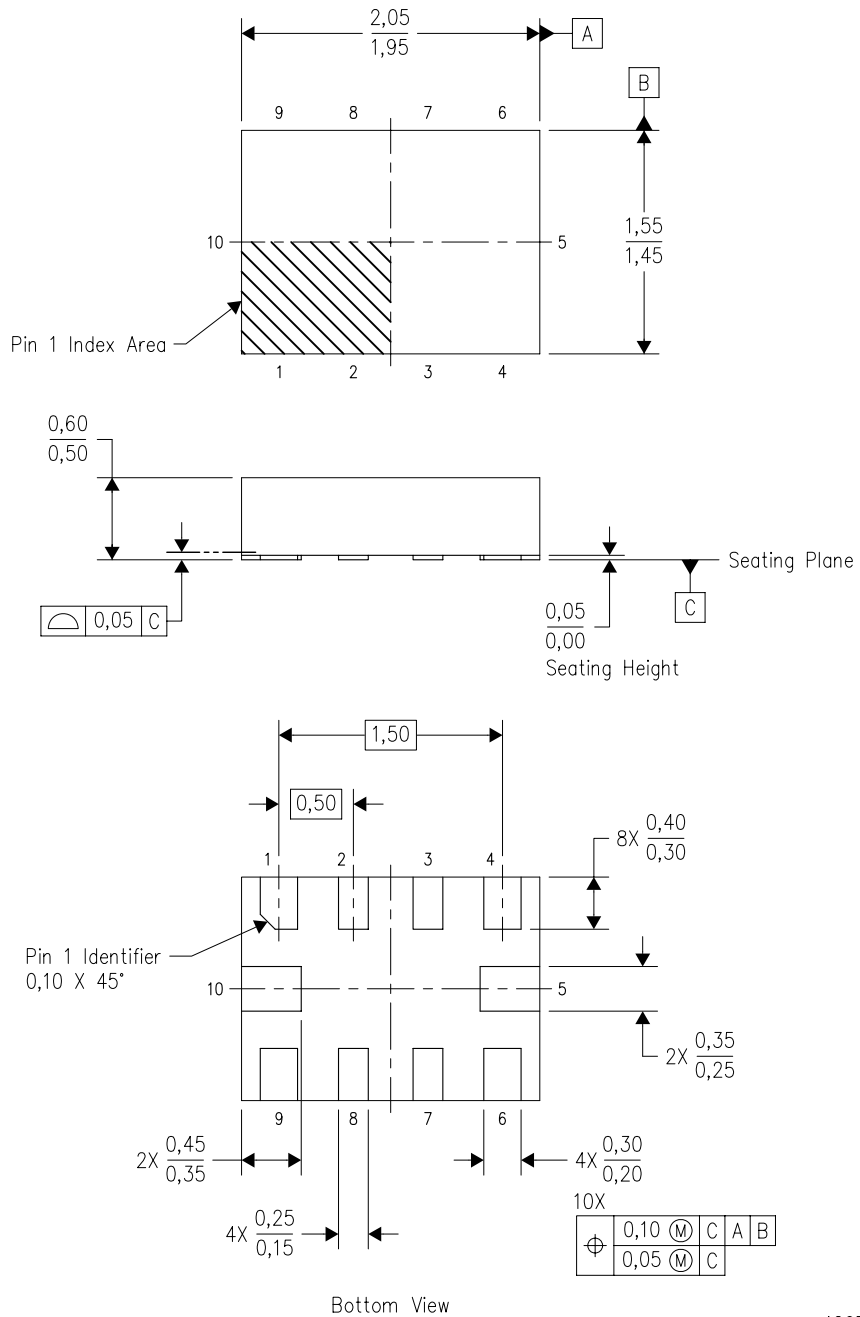
NOTE: A. All linear dimensions are in millimeters





RSE (R-PUQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD

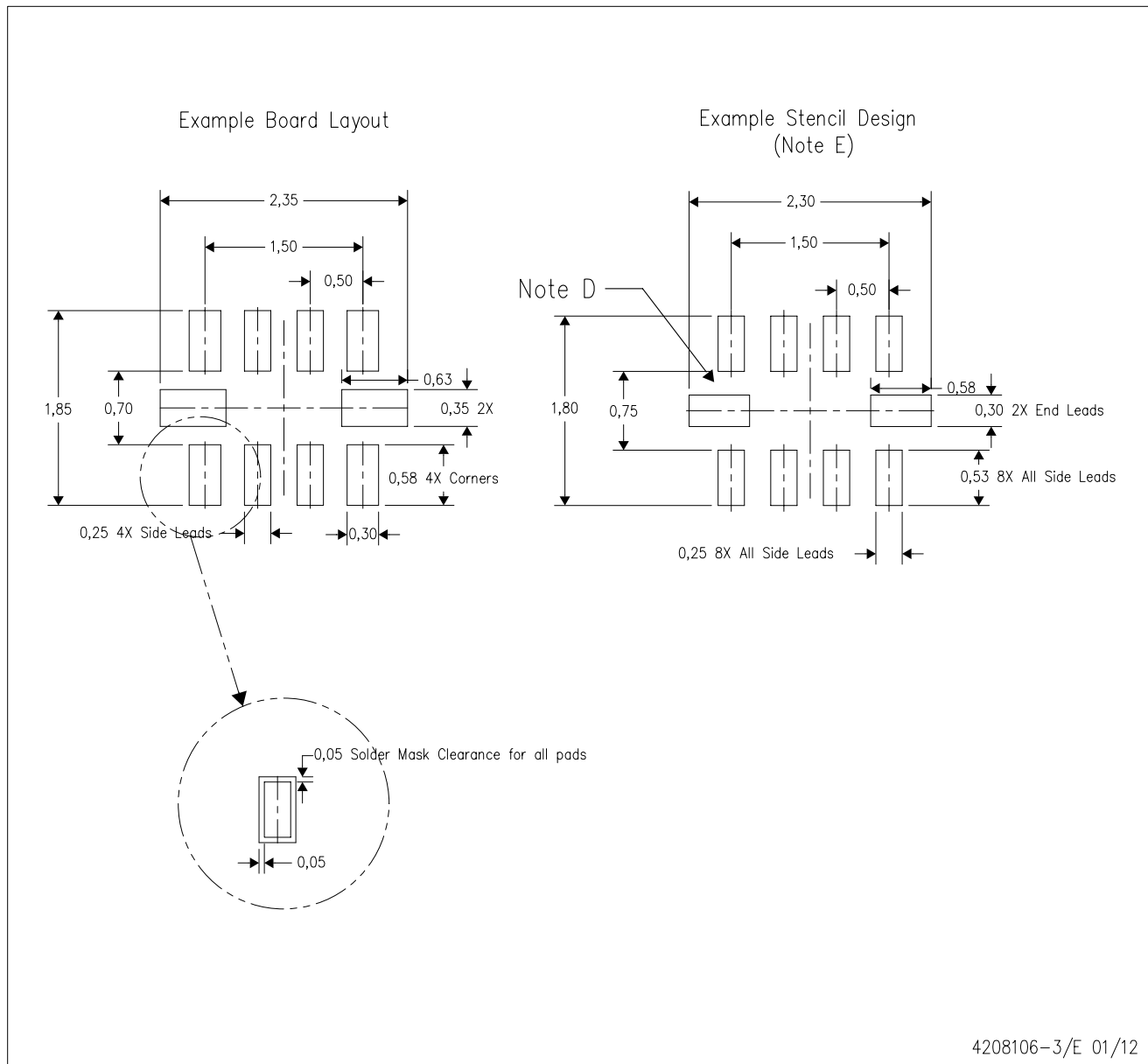


4207268-3/D 01/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. QFN (Quad Flatpack No-Lead) package configuration.
  - D. This package complies to JEDEC MO-288 variation UDFD.

RSE (R-PUQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
  - E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
  - F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
  - G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.

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